



# National Taiwan University

## Sustainable Cerebral Recycled Energy SoC (CERES) Platform Developments and Implementations



## 高效能熱電元件的研製和開發

學生：蔡輔安

指導教授：廖洺漢

台灣大學 機械系

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# Increasing 2D Thermoelectric Cooler efficiency by annealing (1/5)

- The generated voltage by the 2D device can be improved approximately 70% by annealing after the deposited process is done.

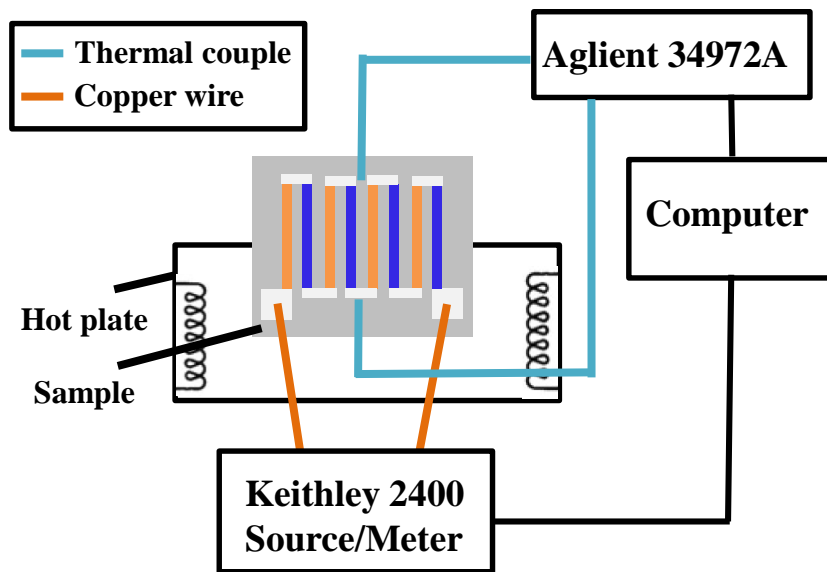


Fig. 1-2. Schematic of the measurement system

- Wafer cleaning in Acetone
- N-type, P-type, connector deposition
- Annealing at  $200^{\circ}\text{C}$  for 120 min
- Electrical properties measurement

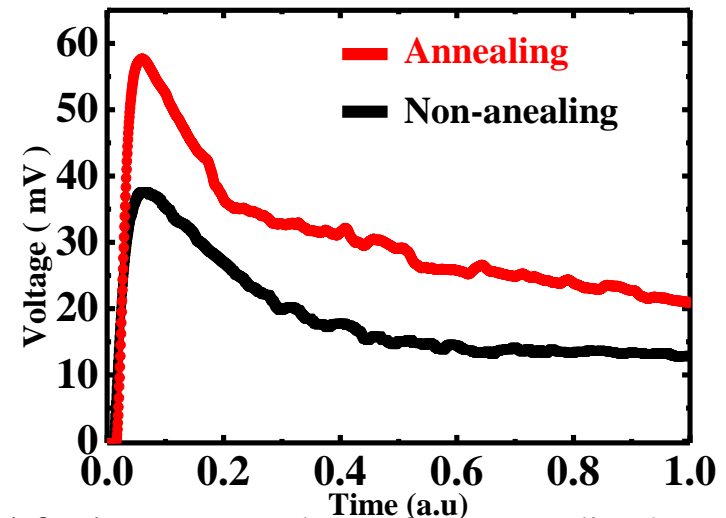


Fig. 1-3. Time versus voltage of non-annealing 2D cooler compared with annealing 2D cooler at 30K temperature difference.

# Electrical Conductivity Measurement for 2D Thermoelectric Cooler(2/5)

- The electrical conductivity of 2D thermoelectric cooler is almost the same as spark plasma sintered  $\text{Si}_{80}\text{Ge}_{20}$  in  $50^\circ\text{C}$ . (Fig. 2-3)

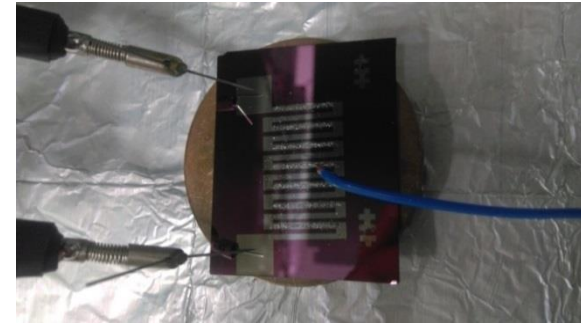


Fig. 2-1. Experimental set-up for determining conductivity

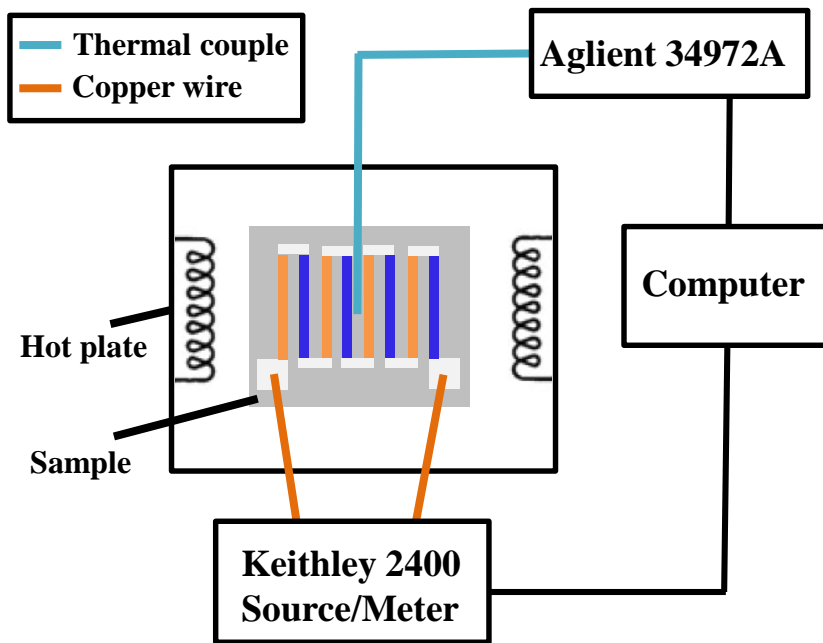


Fig. 2-2. Schematic of the measurement system

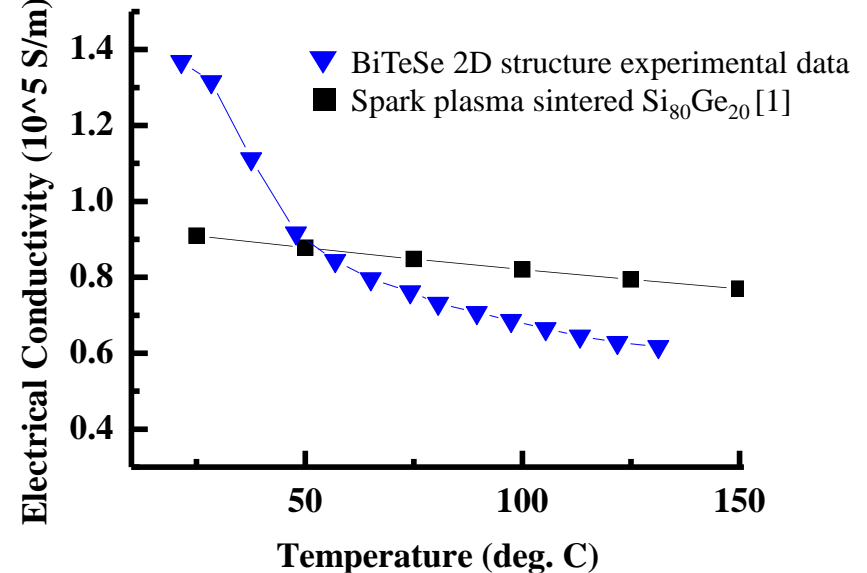


Fig. 2-3. Temperature dependence of the conductivity of 2D cooler compared with spark plasma sintered  $\text{Si}_{80}\text{Ge}_{20}$ .

# Seebeck Coefficient Measurement for 2D Thermoelectric Cooler(3/5)

- Seebeck coefficient determined by measuring electric potential emergent across 2D cooler in a thermal gradient:

$$S_{ab} = \lim_{\Delta T \rightarrow 0} \frac{\Delta V_{ab}}{\Delta T}$$

- The Seebeck coeff. are higher than  $\text{Si}_{80}\text{Ge}_{20}$  in all range temperature.

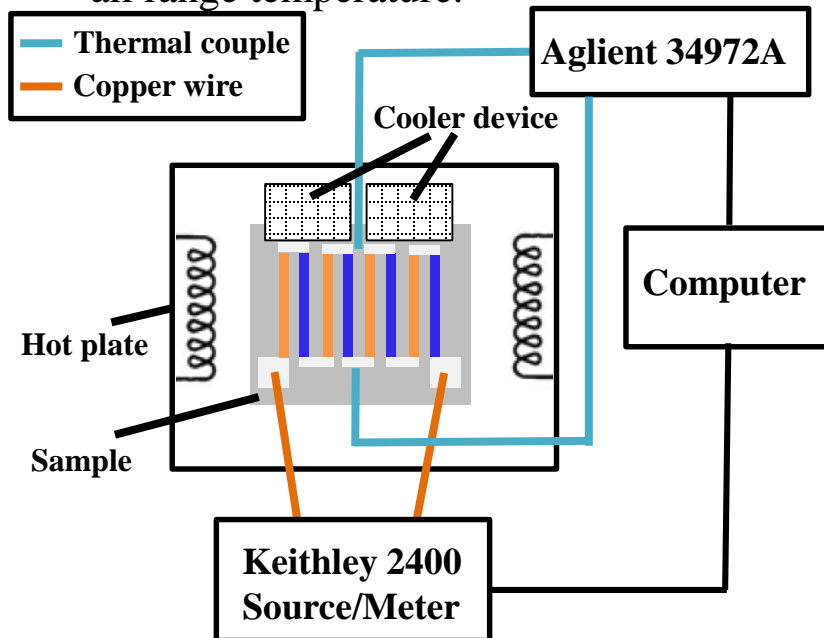


Fig. 3-2. Schematic of the measurement system



Fig. 3-1. Experimental set-up for determining Seebeck Coeff.

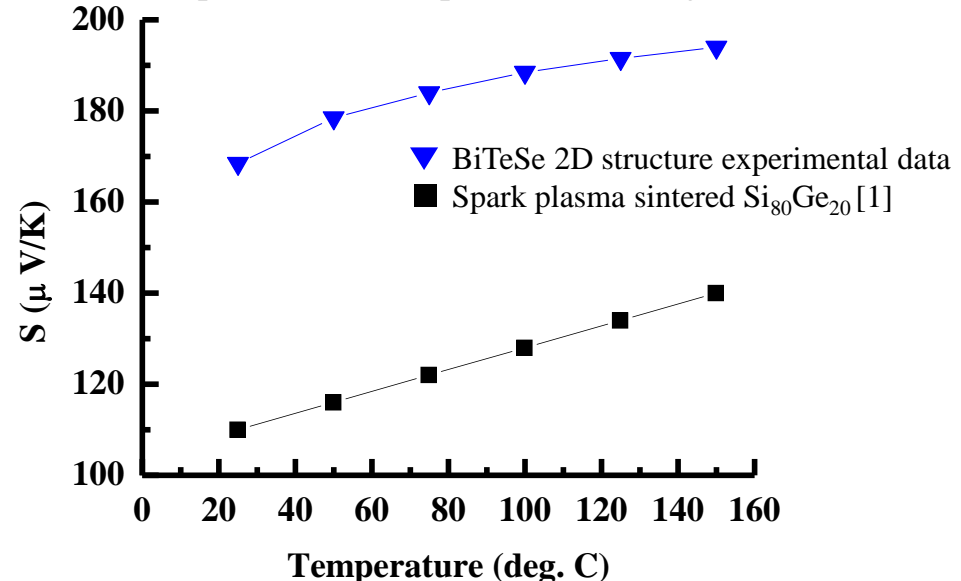


Fig. 3-3. Temperature dependence of the Seebeck coeff. of 2D cooler compared with spark plasma sintered  $\text{Si}_{80}\text{Ge}_{20}$ .

# Power Factor Calculation for 2D Thermoelectric Cooler(4/5)

- Power factor can be determined by the equation below:  $Power\ Factor = \sigma S^2$
- The higher value of power factor is, the more energy the device can generate.
- The power factor of 2D cooler is higher than  $Si_{80}Ge_{20}$  in 25 °C, but it drop quickly near 50°C.

Temperature	Power factor (uW cm-1 k-2)
25	11.74496644
50	12.38390093
75	12.93103448
100	13.40482574
125	13.81909548
150	14.18439716

Fig. 4-1. Power factor data sheet of spark plasma sintered  $Si_{80}Ge_{20}$ .

Temperature	Power factor (uW cm-1 k-2)
32	36.558428
43	31.6266255
61	26.41480536
79	25.01687552
99	24.3040572
122	24.26123504
148	24.04899556

Fig. 4-2. Power factor data sheet of 2D thermoelectric cooler.

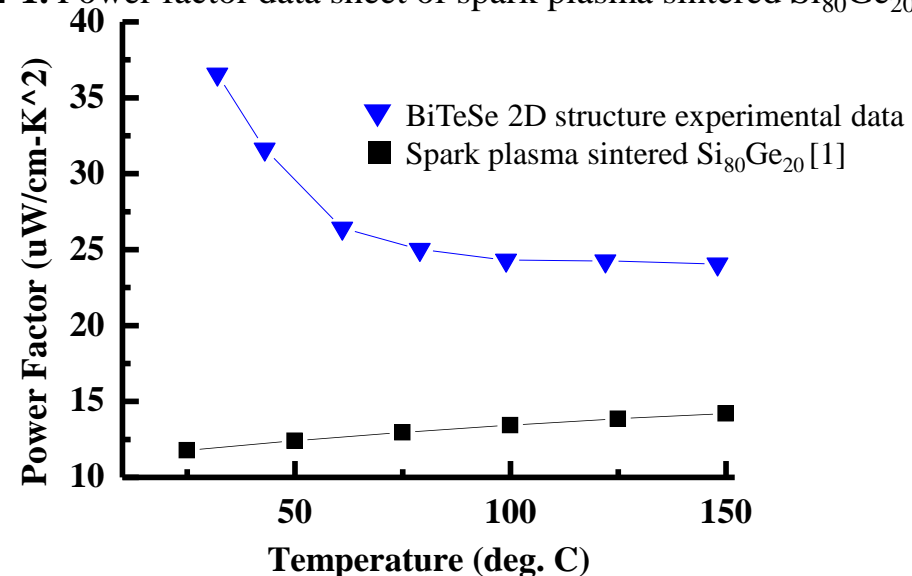
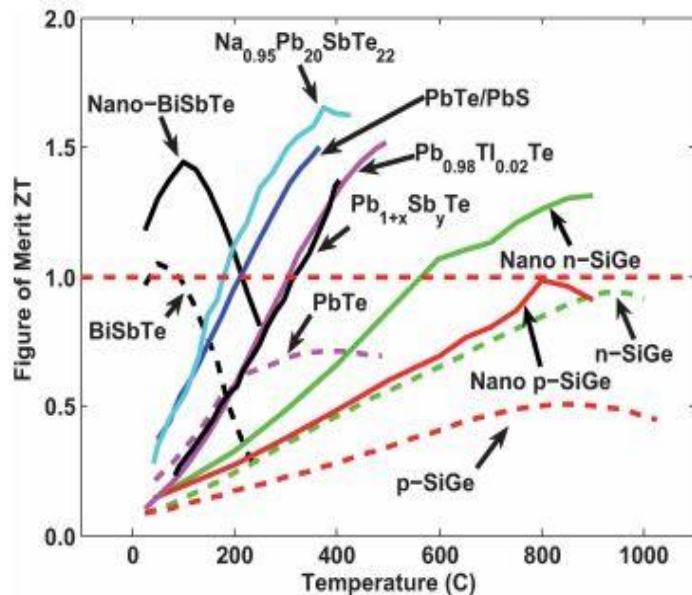


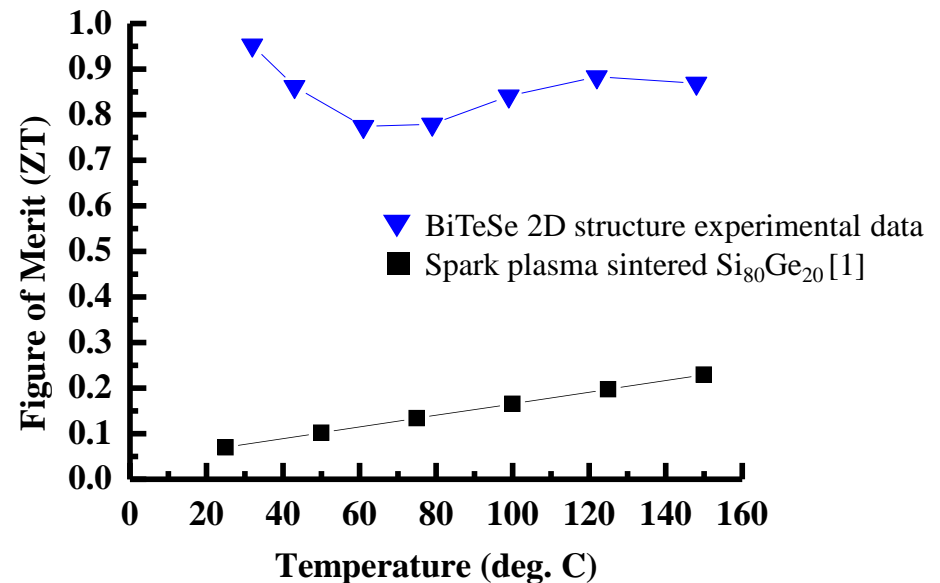
Fig. 4-3. Temperature dependence of the power factor of 2D cooler compared with spark plasma sintered  $Si_{80}Ge_{20}$ .

# Figure of Merit ZT Calculation for 2D Thermoelectric Cooler(5/5)

- The efficiency of thermoelectric device is determined by the dimensionless figure of merit, defined as:  $ZT = \frac{\sigma S^2 T}{k}$ , where  $\sigma$  and  $S$  can be determined from previous page,  $k$  is got from the reference[1,2].
- Compare with the reference, the ZT values of 2D cooler is significantly higher than spark plasma sintered  $\text{Si}_{80}\text{Ge}_{20}$ , so **our device are more efficient than others.**



**Fig. 5-1.** Temperature dependence of the ZT of other materials.



**Fig. 5-2.** Temperature dependence of the ZT of 2D cooler compared with spark plasma sintered  $\text{Si}_{80}\text{Ge}_{20}$ .

[1] A. Lahwal, X. Zeng, S. Bhattacharya, M. Zhou, D. Hitchcock, M. Enhancing Thermoelectric Properties of  $\text{Si}_{80}\text{Ge}_{20}$  Alloys Utilizing the Decomposition of  $\text{NaBH}_4$  in the Spark Plasma Sintering Process. *Energies*. 2017, 8, 10958-10970